L Number	Hits	Search Text	DB	Time stamp
157	16	("3629088" "4277320" "4300989" "4636400" "4715937" "4917843" "5376593" "5445999" "5618755" "5747357" "5907792" "5913149" "5989338" "6077754" "6087229"	USPAT	2004/03/05 09:41
-	6	"6136388").PN. (("6077257") or ("6077751") or ("6303520")).PN.	USPAT; US-PGPUB;	2004/03/01 13:29
-	69	kick adj out adj mechanism	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/06/04 13:40
-	61	(kick adj out adj mechanism) and @ad<=19990503	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/04 13:40
		5454700 UDDN	IBM_TDB	0000/00/04 44:00
-	9	5151766.URPN. ("3888701" "3933527" "4056408" "4115798" "4240844" "4249962" "4278475" "4406709" "4987087").PN.	USPAT USPAT	2002/06/04 14:29 2002/06/04 14:30
-	5887	((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 11:29
-	5109	(257/219) or (257/609) or (257/617) or (257/649)).CCLS. (((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/04 15:05
-	1867	(257/219) or (257/609) or (257/617) or (257/649)).CCLS.) and @ad<=19990503 (control controlling controlled controls) same (defect vancancy) same (gas)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/04 15:09
-	168	((control controlling controlled controls) same (defect vancancy) same (gas)) and ((silicon adj oxynitride) (silicon adj nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2002/06/05 13:16
-	8	("4705591" "4755865" "4766477" "4772927" "4968384" "4998150" "5463978" "5683934").PN.	USPAT	2002/06/04 17:13
-	4	(boron b) and (defect adj enhanced adj diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:23
-	4	(boron b arsenic as antimony sb indium in) and (defect adj enhanced adj diffusion)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/06/05 11:26
-	4	(boron b arsenic as antimony sb indium in) and ((defect trasient) adj enhanced adj diffusion)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:28

-	5436	(boron b arsenic as antimony sb indium in) and (((defect trasient) adj enhanced adj diffusion) gettering)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:29
-	6409	((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:30
-	5557	(((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/797) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.) and @ad<=19990503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:31
-	1208	((((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.) and @ad<=19990503) and ((silicon adj oxynitride) siono sion (silicon adj nitride) sin)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:32
_	328	(((((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.) and @ad<=19990503) and ((silicon adj oxynitride) siono sion (silicon adj nitride) sin)) and (control same (gas temperature	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 11:49
-	150	thermal concentration pressure)) ((((((438/795) or (438/796) or (438/797) or (438/798) or (438/799) or (438/492) or (438/477) or (438/766) or (438/769) or (438/775) or (438/778) or (438/786) or (438/791) or (438/5) or (257/55) or (257/63) or (257/171) or (257/219) or (257/609) or (257/617) or (257/649) or (438/143) or (438/476) or (438/472) or (438/473)).CCLS.) and @ad<=19990503) and ((silicon adj oxynitride) siono sion (silicon adj nitride) sin)) and (control same (gas temperature thermal concentration pressure))) and (defect vacancy vacant) and (creation generation generate formation forming formed creates created)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:01
-	986	(generating creating) adj defect	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:02
-	105	((generating creating) adj defect) and (semiconductor with material)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:07
-	83	(((generating creating) adj defect) and (semiconductor with material)) and @ad<=19990503	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/05 13:08

			LUODAT	1 0000/00/05 40 00
-	21	((((generating creating) adj defect) and (semiconductor with	USPAT;	2002/06/05 13:08
		material)) and @ad<=19990503) and (silicon adj (nitride	US-PGPUB;	
		oxynitride))	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	423	((control controlling controlled controls) same (defect	USPAT;	2002/06/05 13:20
		vancancy) same (temperature (partial adj pressure)) and	US-PGPUB;	
		((silicon adj oxynitride) (silicon adj nitride)))	EPO; JPO;	
		(DERWENT;	
			IBM TDB	
	319	(((control controlling controlled controls) same (defect	USPAT;	2002/06/05 13:20
-	319	vancancy) same (temperature (partial adj pressure)) and	US-PGPUB;	2002/00/03 13.20
			EPO; JPO;	
1		((silicon adj oxynitride) (silicon adj nitride)))) and		·
1		@ad<=19990503	DERWENT;	
			IBM_TDB	0000/00/05 40 04
-	273	((((control controlling controlled controls) same (defect	USPAT;	2002/06/05 13:21
		vancancy) same (temperature (partial adj pressure)) and	US-PGPUB;	
		((silicon adj oxynitride) (silicon adj nitride)))) and	EPO; JPO;	
		@ad<=19990503) and thickness	DERWENT;	
]		IBM_TDB	
-	176	(((((control controlling controlled controls) same (defect	USPAT;	2002/06/05 13:21
	1	vancancy) same (temperature (partial adj pressure)) and	US-PGPUB;	
		((silicon adj oxynitride) (silicon adj nitride))))) and	EPO; JPO;	
		@ad<=19990503) and thickness) and concentration	DERWENT;	,
		Wad 1= 10000000) and unokness) and concentration	IBM_TDB	
İ	34	/////control controlling controlled controls) some /defect	USPAT;	2002/06/05 13:22
-	34	((((((control controlling controlled controls) same (defect		2002/00/03 13.22
		vancancy) same (temperature (partial adj pressure)) and	US-PGPUB;	
		((silicon adj oxynitride) (silicon adj nitride)))) and	EPO; JPO;	
		@ad<=19990503) and thickness) and concentration) and	DERWENT;	
		(thermal with stress)	IBM_TDB	
-	33	(lattice with defects with control\$3) and 438/\$.ccls.	USPAT;	2002/11/25 10:35
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	•
			IBM_TDB	
-	11	((lattice with defects with control\$3) and 438/\$.ccls.) and	USPAT;	2002/11/25 10:36
		atmosphere	US-PGPUB;	•
	i	,	EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
	0	(deffect adj enhanced adj diffusion) and (((438/\$)	USPAT	2002/11/30 11:36
-			301 71	2002/11/00 11.00
1		(257/\$)).ccls.)	LICOAT	2002/11/30 13:00
-	4	(defect adj enhanced adj diffusion) and (((438/\$)	USPAT	2002/11/30 13:00
	_	(257/\$)).ccls.)	LIGRAT	0000/44/00 40 00
-	6	("5216271" "5285088" "5432366" "5569624" "5955745"	USPAT	2002/11/30 12:38
	_	"6048756"). PN.	l <u>-</u>	
-	2	(defect adj enhanced adj diffusion) and silicon adj (nitride	USPAT	2002/11/30 13:00
		oxynitride)		
-	2	(defect adj enhanced adj diffusion) and (silicon adj (nitride	USPAT	2002/11/30 13:11
		oxynitride))		
-	8	("4705591" "4755865" "4766477" "4772927" "4968384"	USPAT	2002/11/30 13:01
]	"4998150" "5463978" "5683934").PN.		
-	0	((defect adj enhanced adj diffusion) and (silicon adj (nitride	USPAT	2002/11/30 13:09
		oxynitride))) and (outdiffusion (out adj diffusion))		
1_	91	((defect transient) with enhanced with diffusion) and (silicon	USPAT	2002/11/30 13:12
l		adj (nitride (oxy adj nitride) oxynitride))	331 / (1	2002/11/00 10.12
_	53	((((defect transient) with enhanced with diffusion) and (silicon	USPAT	2002/11/30 13:13
1	33		JOFAI	2002/11/30 13.13
		adj (nitride (oxy adj nitride) oxynitride))) and		
	·	@ad<=19990503	LIGDAT	0000/44/00 40 40
-	32	((((defect transient) with enhanced with diffusion) and (silicon	USPAT	2002/11/30 13:13
		adj (nitride (oxy adj nitride) oxynitride))) and		
		@ad<=19990503) and control		

_	3	(((((defect transient) with enhanced with diffusion) and	USPAT	2002/11/30 13:14
]		(silicon adj (nitride (oxy adj nitride) oxynitride))) and		
		@ad<=19990503) and control\$4) and (outdiffusion (out adj		
		diffusion) outdiffused)		
_	14	("4841346" "5478763" "5500379" "5543337" "5578510"	USPAT	2002/11/30 13:16
	· ·	"5851886" "5874329" "5893740" "6010952" "6020231"		
	ļ	"6020244" "6025232" "6030875" "6051860").PN.		
	43	((((defect transient) with enhanced with diffusion) and (silicon	USPAT	2002/11/30 13:35
-	1 43		USFAI	2002/17/30 13:33
	1	adj (nitride (oxy adj nitride) oxynitride))) and		,
		@ad<=1990503) and control\$4	LICDAT	2002/44/20 42:20
-	1	((((((((((((((((((((USPAT	2002/11/30 13:39
		adj (nitride (oxy adj nitride) oxynitride))) and		
		@ad<=19990503) and control\$4 with gas\$4	l <u></u>	
-	184	lerch.inv.	USPAT	2002/11/30 13:39
-	1	lerch.inv. and rtp.as.	USPAT	2002/11/30 13:39
-	1	lerch.inv. and steag.as.	USPAT	2002/11/30 13:39
-	299	((438/413) or (438/419)).CCLS.	USPAT;	2002/11/30 13:57
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	·
			IBM_TDB	İ
_	101	(((438/413) or (438/419)).CCLS.) and silicon adj nitride	USPAT;	2002/11/30 14:12
			US-PGPUB;	
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
_	0	((((438/413) or (438/419)).CCLS.) and silicon adj nitride) and	USPAT;	2002/11/30 13:58
		outdiffusion with prevent\$3	US-PGPUB;	
		outum proventes	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
	2	((((438/413) or (438/419)).CCLS.) and silicon adj nitride) and	USPAT;	2002/11/30 13:59
	-	((ut with diffusion) with prevent\$3	US-PGPUB;	2002/11/00 10:00
		(out with diffusion) with preventuo	EPO; JPO;	
			DERWENT,	
		·	IBM_TDB	
	15	3929528.URPN.	USPAT	2002/11/30 14:00
-	0	(((438/413) or (438/419)).CCLS.) and (silicon adj nitride) with	USPAT;	2002/11/30 14:00
_	l "		US-PGPUB;	2002/11/30 14.13
		(outdiffusion (out adj diffusion))		
			EPO; JPO; DERWENT;	·
	1-	420/0	IBM_TDB	2002/44/20 44:40
-	47	438/\$.ccls. and (silicon adj nitride) with (outdiffusion (out adj	USPAT;	2002/11/30 14:13
		diffusion))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	36	(438/\$.ccls. and (silicon adj nitride) with (outdiffusion (out adj	USPAT;	2002/11/30 14:14
		diffusion))) and @ad<=19990503	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	·
	ļ		IBM_TDB	
-	6	(("5387548") or ("5967794") or ("6319779")).PN.	USPAT;	2002/11/30 16:02
			US-PGPUB;	
			EPO; JPO;	
	Ì		DERWENT;	
			IBM_TDB	

-	6293	((438/5) or (438/289) or (438/290) or (438/301) or (438/307)	USPAT;	2003/07/08 09:05
		or (438/471) or (438/522) or (438/530) or (438/916) or	US-PGPUB	
		(438/920) or (438/for.445) or (257/55) or (257/63) or		
		(257/191) or (257/219) or (257/609) or (257/617) or		
		(257/649) or (438/795) or (438/472) or (438/477) or		
		(438/766) or (438/769) or (438/775) or (438/778) or		
		(438/786) or (438/791) or (438/796) or (438/797) or		•
		(438/798) or (438/799) or (438/143) or (438/476) or]	
		(438/472) or (438/473) or (438/477)).CCLS.		
_	2989	(((438/5) or (438/289) or (438/290) or (438/301) or (438/307)	USPAT:	2003/07/08 09:06
	2000	or (438/471) or (438/522) or (438/530) or (438/916) or	US-PGPUB	
		(438/920) or (438/for 445) or (257/55) or (257/63) or	00 / 0. 05	
		(257/191) or (257/219) or (257/609) or (257/617) or		
		(257/649) or (438/795) or (438/472) or (438/477) or		
		(438/766) or (438/769) or (438/775) or (438/778) or		
		(438/786) or (438/791) or (438/796) or (438/797) or		
		(438/798) or (438/799) or (438/143) or (438/476) or		
	204	(438/472) or (438/473) or (438/477)).CCLS.) and control	USPAT:	2002/07/09 44:05
-	391	(((438/5) or (438/289) or (438/290) or (438/301) or (438/307)	USPAT; US-PGPUB	2003/07/08 11:25
		or (438/471) or (438/522) or (438/530) or (438/916) or	US-PGPUB	
1		(438/920) or (438/for.445) or (257/55) or (257/63) or		
1		(257/191) or (257/219) or (257/609) or (257/617) or		
		(257/649) or (438/795) or (438/472) or (438/477) or		
i		(438/766) or (438/769) or (438/775) or (438/778) or		
		(438/786) or (438/791) or (438/796) or (438/797) or		
		(438/798) or (438/799) or (438/143) or (438/476) or		1
		(438/472) or (438/473) or (438/477)).CCLS.) and control\$4		•
		with (concentration pressure temperature) with (dopant		
		impurity doping)	LIODAT	0000/07/00 00.00
[-	77	((((438/5) or (438/289) or (438/290) or (438/301) or (438/307)	USPAT;	2003/07/08 09:09
		or (438/471) or (438/522) or (438/530) or (438/916) or	US-PGPUB	
		(438/920) or (438/for.445) or (257/55) or (257/63) or		
		(257/191) or (257/219) or (257/609) or (257/617) or		
		(257/649) or (438/795) or (438/472) or (438/477) or		
		(438/766) or (438/769) or (438/775) or (438/778) or		
		(438/786) or (438/791) or (438/796) or (438/797) or		
		(438/798) or (438/799) or (438/143) or (438/476) or		,
		(438/472) or (438/473) or (438/477)).CCLS.) and control\$4		
		with (concentration pressure temperature) with (dopant		
		impurity doping)) and gas with atmosphere		0000/07/00 44 55
-	17	(((438/5) or (438/289) or (438/290) or (438/301) or (438/307)	USPAT;	2003/07/08 11:25
		or (438/471) or (438/522) or (438/530) or (438/916) or	US-PGPUB	
		(438/920) or (438/for.445) or (257/55) or (257/63) or		
		(257/191) or (257/219) or (257/609) or (257/617) or		
		(257/649) or (438/795) or (438/472) or (438/477) or		
		(438/766) or (438/769) or (438/775) or (438/778) or		
		(438/786) or (438/791) or (438/796) or (438/797) or		
		(438/798) or (438/799) or (438/143) or (438/476) or		·
		(438/472) or (438/473) or (438/477)).CCLS.) and control\$4		
		with (outdiffusion ("out diffusion"))		
-	7383	control\$4 with (concentration pressure temperature) with	USPAT;	2003/07/08 11:26
		(dopant impurity doping)	US-PGPUB	
	201	control\$4 with (outdiffusion ("out diffusion"))	USPAT;	2003/07/08 11:26
		··	US-PGPUB	
-	57	(control\$4 with (concentration pressure temperature) with	USPAT;	2003/07/08 13:37
		(dopant impurity doping)) and (control\$4 with (outdiffusion	US-PGPUB	
		("out diffusion")))	·	
		(out aimusion")))	<i>:</i>	L

			LIODAT	0000/07/00 44:00
-	8	((((438/5) or (438/289) or (438/290) or (438/301) or (438/307)	USPAT;	2003/07/08 11:26
		or (438/471) or (438/522) or (438/530) or (438/916) or	US-PGPUB	
		(438/920) or (438/for.445) or (257/55) or (257/63) or		
		(257/191) or (257/219) or (257/609) or (257/617) or		
		(257/649) or (438/795) or (438/472) or (438/477) or		
		(438/766) or (438/769) or (438/775) or (438/778) or		
		(438/786) or (438/791) or (438/796) or (438/797) or		
		(438/798) or (438/799) or (438/143) or (438/476) or		
		(438/472) or (438/473) or (438/477)).CCLS.) and control\$4		
		with (outdiffusion ("out diffusion"))) and ((control\$4 with		
		(concentration pressure temperature) with (dopant impurity		
		doping)) and (control\$4 with (outdiffusion ("out diffusion"))))		
-	7	5569615.URPN.	USPAT	2003/07/08 13:19
	6	("4780424" "4861730" "5114876" "5158903" "5180690" "5569615").PN.	USPAT	2003/07/08 13:22
-	57	(control\$4 with (concentration pressure temperature) with	USPAT;	2003/07/08 13:39
		(dopant impurity doping)) and (control\$4 with (outdiffusion	US-PGPUB	
		("out diffusion")))		
-	7241	dop\$3 with profile	USPAT;	2004/02/27 14:07
			US-PGPUB	
-	912	thermal with process with (ammonia "nh.sub.3" "no.sub.2")	USPAT;	2004/02/27 14:07
			US-PGPUB	
1 -	17	(dop\$3 with profile) and (thermal with process with (ammonia	USPAT;	2004/02/27 14:08
		"nh.sub.3" "no.sub.2"))	US-PGPUB	
-	321	forming with silicon with (nitride or oxynitride) with doped with	USPAT;	2004/03/01 13:32
		substrate	US-PGPUB	
-	10	forming with silicon with (nitride or oxynitride) with doped with	USPAT;	2004/03/01 13:36
		substrate with thickness with ("2" or "4")	US-PGPUB	
-	24	(forming with silicon with (nitride or oxynitride) with doped	USPAT;	2004/03/01 13:37
		with substrate) and thickness with ("2 nm" or "20 angstroms"	US-PGPUB	
		or "4 nm" or "40 angstroms")		
-	16	("3629088" "4277320" "4300989" "4636400" "4715937"	USPAT	2004/03/01 15:20
		"4917843" "5376593" "5445999" "5618755" "5747357"		
		"5907792" "5913149" "5989338" "6077754" "6087229"		
		"6136388").PN.	LICOAT	0004/00/04 46 54
-	16	("3629088" "4277320" "4300989" "4636400" "4715937"	USPAT	2004/03/04 10:51
		"4917843" "5376593" "5445999" "5618755" "5747357"		
		"5907792" "5913149" "5989338" "6077754" "6087229"		
		"6136388").PN.	110047	0004/00/04 44:00
-	18	6087229.URPN.	USPAT	2004/03/04 11:38
-	11	("4621277" "4913929" "5258333" "5422291" "5464783"	USPAT	2004/03/04 11:43
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		"5969397").PN.	HCDAT	2004/02/04 14:50
-	23	5422291.URPN.	USPAT	2004/03/04 11:52
-	11	5600166.URPN.	USPAT	2004/03/04 11:55 2004/03/04 11:55
-	18	6087229.URPN.	USPAT	2004/03/04 11:55